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Attorney Docket No. P120-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Shi, et al.

Art Unit: Not Yet Assigned

Serial No.: 10/666,002

Examiner: Not Yet Assigned

Filed: 9/17/03

For: **AN ETCHING METHOD USED IN FABRICATIONS OF MICROSTRUCTURES**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
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Alexandria, VA 22313-145

Sir:

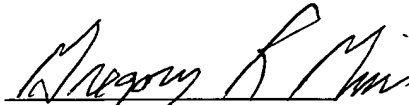
The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

The Patent Office is authorized to charge our Deposit Account No. 501516 for any fee which it deems to be required to effect consideration of this statement.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Gregory R. Muir", written over a horizontal line.

Gregory R. Muir
Attorney for Applicant(s)
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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Complete if Known	
		Application Number	10/666,002
		Filing Date	9/17/03
		First Named Inventor	Shi
		Art Unit	Not Yet Assigned
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Attorney Docket Number	P120-US		
Sheet	1	of	6

U.S. PATENT DOCUMENTS					
Examiner Initials [*]	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
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		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
		US- 6,162,367	12-19-2000	Tai et al.	
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		US- 2001/0002663 A1	06-07-2001	Tai et al.	
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		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
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		US- 5,726,480	03-10-1998	Pister, K.S.	
		US- 2002/0185699	12-12-2002	Reid	
		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
		US- 5,835,256	11-10-1998	Huibers, A.	
		US- 2002/0047172 A1	04-25-2002	Reid	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials [*]	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
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		EP-0878824-A2	11-18-1998	McQuarrie et al.		
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		JP-1982/57098679-A	06-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A	08-04-1983	Yoshihiro et al.		
		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32163	07-23-1998	Tai et al.		

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		Number - Kind Code ² (if known)			
		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leung, et al.	
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		US- 2004/0035821	2/26/04	Doan, et al.	
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		JP-1986/61187238-A	08-20-1986	Nobuo et al.		
		JP-1986/61270830-A	12-01-1986	Toru, T.		
		JP-1987/62071217-A	04-01-1987	Toru et al.		
		JP-1988/63155713-A	06-28-1988	Tadashi, F.		
		JP-1986/61053732-A	03-17-1986	Arata et al.		
		JP-1986/61134019-A	06-21-1986	Shinji et al.		
		JP-1986/61181131-A	08-13-1986	Shinji et al.		

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				Filing Date	9/17/03
				First Named Inventor	Shi
				Art Unit	Not Yet Assigned
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		US-			
		US-			
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP-1989/01208834-A	08-22-1989	Nobuo et al.		
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		JP-1990/02250323-A	10-08-1990	Susumu et al.		
		JP-1991/03012921-A	01-21-1991	Nobuo et al.		
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		JP-1995/07029823-A	01-31-1995	Hiroshi, T.		

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/666,002	
			Filing Date	9/17/03	
			First Named Inventor	Shi	
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F2 and XeF2 Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
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		HABUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6466-6469.	
		HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO2 Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5256-5261.	
		HOULE, F.A., "Dynamics of SiF4 Desorption During Etching of Silicon by XeF2", IBM Almaden Research Center (April 15, 1987), pp. 1866-1872.	
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		IBBOTSON et al., "Plasmaless Dry Etching of Silicon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 10 (Nov. 1984), pp. 2939-2942.	
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		VUGTS et al., "Si/XeF2 Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
		WINTERS, H.F., "Etch Products from the Reaction of XeF2 with SiO2, SiO3, Si3N4, SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	

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			Filing Date	9/17/03	
			First Named Inventor	Shi	
			Group Art Unit	Not Yet Assigned	
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Sheet	5	of	6	Attorney Docket Number	P120-US

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T²
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF ₂ Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
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		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
		BASSOM et al., "Modeling and Optimizing XeF ₂ -enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
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		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millenium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
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		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5-μm CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed XeF ₂ Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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